

Title (en)  
Semiconductor injection laser or intensifier.

Title (de)  
Halbleiter-Injektionslaser oder-verstärker.

Title (fr)  
Laser ou amplificateur à injection à semiconducteurs.

Publication  
**EP 0000412 A2 19790124 (EN)**

Application  
**EP 78200074 A 19780703**

Priority  
NL 7707720 A 19770712

Abstract (en)  
A semiconductor laser or traveling wave intensifier having an active layer between two passive semiconductor layers, and a strip-shaped electrode geometry. According to the invention the active layer is uniform in thickness. while at least one of the passive layers within the strip-shaped geometry comprises a strip-shaped zone of deviating construction and is built up from portions having different refractive indices  $n$ , and  $n_{<sub>2</sub>}$ . According to the invention it holds that wherein  $n$ , is the refractive index of the portion which at least within said strip-shaped zone adjoins the active layer,  $d$ , is the thickness thereof within the strip-shaped zone, and  $d_{<sub>2</sub>}$  is the thickness thereof beside the strip-shaped zone.

IPC 1-7  
**H01S 3/19**

IPC 8 full level  
**H01S 5/22** (2006.01); **H01S 5/223** (2006.01); **H01S 5/00** (2006.01); **H01S 5/50** (2006.01)

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Cited by  
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DE FR GB NL SE

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DOCDB simple family (application)  
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